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Documents: 492

Citations: 10 737 total citations by 5474 documents

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* 1. **JOURNAL PAPERS (276)**

**2021**

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List of invited papers followed by Journal papers and Conference papers:

**1.2 INVITED and TUTORIAL (117)**

1. *(tutorial)*W. Knap, et al, **"Transistors based THz detectors - from basic physics to first real world applications."**, European Solid Deuce Research Conference, Cracow, Poland, 22–26 September, 2019
2. *(tutorial)*W. Knap, et al, **"Terahertz Plasma Oscillations in Field Effect Transistors: from Basic Physics to Applications (>25 Years History)."**, 8th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & GDR-I FIR-LAB Workshop Nizhny Novgorod, Nizhny Novgorod, Russia, 8 August, 2019
3. *(invited)*W. Knap, et al, **"THz cyclotron emission from bulk HgCdRe alloys."**, 29th International Travelling Summer School (ITSS) on Microwaves and Lightwaves, Frankfurt, Germany, 13–19 July, 2019
4. *(invited)*W. Knap, et al, **"THz cyclotron emission from Dirac-like fermions in bulk HgCdTe."**, International Workshop of FIR-LAB network, Nizhny Novgorod, Russia, 7 July, 2019
5. *(tutorial)*W. Knap, et al, **"Tutorial Terahertz plasma oscillations in Nanotransistors-Basic Science and Applications."**, XXIII International Symposium "Nanophysics & Nanoelectronics" Nizhny Novgorod, Nizhny Novgorod, Russia, 10–14 March, 2019
6. *(invited)*W. Knap, et al, **"Field Effect Transistors Based Terahertz Detectors 25 Years History, State of the Art and Future Directions."**, 43rd International Conference on Infrared, Milimeter and Terahertz Waves, Nagoya, Japan, 9–14 September, 2018
7. *(invited)*W. Knap, et al, **"New GaN FETs and Silicon Junctionless Field Effect Transistor Terahertz Detectors."**, Frontiers of photonics, plasmonics and electronics with 2D nanosystems, Erice, Italy, 14–20 July, 2018
8. *(invited)*W. Knap, et al, **"New GaN and Silicon Junctionless Field Effect Transistor Terahertz Detectors."**, 9th International Conference Materials Science and Condensed Matter Physics, Chisinau, Republic of Moldova, 25–28 September, 2018
9. *(oral)*W. Knap, et al, **"Topological Phases of HgTe Quantum Wells for QHE resistance standard applications."**, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop, Warsaw, Poland, 17–21 September, 2018
10. *(oral)*W. Knap, et al, **"EdgeFET Based on AlGaN/GaN with Two Lateral Schottky Barrier Gates Towards Resonant Terahertz Detection."**, 7th Russia-Japan-USA-Europe Symposium on Fundamental & Applied Problems of Terahertz Devices & Technologies & 4th TERAMIR International Laboratory Workshop, Warsaw, Poland, 17–21 September, 2018
11. *(invited)*W. Knap, et al, **"Terahertz Vision Using Field Effect Transistors Detectors Arrays"**, 22nd International Microwave and Radar Conference (MIKON 2018), Poznan, Poland, 15–17 May, 2018
12. *(invited)*W. Knap, et al, **"Terahertz imaging and wireless communication with nanometer field effect transistor arrays"**, International Symposium on Photonics and Optical Communications (ISPOC 2017) Katahira - Sendai - Japan, 25-26 October, 2017
13. *(invited)*W. Knap, et al, **“Terahertz Imaging With GaAs and GaN Plasma Field Effect Transistors Detectors Arrays”**, 4th International Symposium on Microwave and Terahertz Science and Applications 2017, Okayama- Japan, November 19-23, 2017
14. *(plenary)*W. Knap, et al, **“Terahertz Imaging and Wireless Communication with Nanometer Field Effect Transistor Arrays”**, 17 th International Conference on Emerging Technologies ETMOS , Warsaw, May 28 - 30, 2017
15. *(invited)*W. Knap, D. But, F. Teppe J. Suszek, A. M. Siemion, M. Sypek, G. Cywinski, **“Terahertz Plasma Field Effect Transistors: From Basic Physics to First Postal Scanners Imaging Applications”**, 46rd European Microwave Conference 2016, London, October 3-7, 2016
16. *(plenary)*W. Knap, et al **“PLASMA FIELD EFFECT TRANSISTOR ARRAYS FOR IMAGING IN SUB-THZ ATMOSPHERIC WINDOWS”**, 5th Russia-Japan-USA-Europe Symposium on Fundamental and Applied Problems of Terahertz Devices and Technologiers RJUSE TeraTech 2016, Sendai- Japan , Oct 31-Nov 1 June, 2016
17. *(plenary)*W. Knap et al., **“Terahertz Plasma FETs - First Imaging Applications”**, Emerging Technologies 2016 Conference, Montreal, May 25 – 27, 2016
18. *(plenary)*W. Knapet al., **“Terahertz Plasma Field Effect Transistors: From Basic Physics to First Imaging Applications”**, International Workshop on "Terahertz Science, Nanotechnologies and Applications" – Erice (Sicily), Italy - July 16-22, 2016
19. *(invited)*W. Knap, N. Dyakonova, D. But, F. Teppe J. Suszek, A. M. Siemion, M. Sypek, G. Cywinski, K. Szkudlarek, I. Yahniuk, **“Terahertz Imaging With GaAs and GaN Plasma Field Effect Transistors Detectors Arrays”**, 23rd International Conference Mixed Design of Integrated Circuits and Systems MIXDES 2016, Lodz, 23-25 June, 2016
20. *(plenary)* W. Knap, B. Moulin, M. Sypek, D. Coquillat, G. Cywinski, J. Suszek, M. Triki, D. But, A.Siemion, K. Szkudlarek, C. Archier, N. Dyakonova, T. Antonini, F. Teppe **“Plasma Field Effect Transistors Arrays for Amplitude and Polarization Imaging in THz Range”**, 8th International Conference on Materials Science and Condensed Matter Physics, September 12-16, 2016, Chisinau, Moldova
21. W. Knap, D. But, D. Coquillat, N. Dyakonova, F. Teppe, **“Terahertz Imaging by Field Effect Transistors”**, Conference 21st International Conference on Microwave, Radar and Wireless Communications, MIKON 2016, May 9-11, Krakow, 2016
22. W. Knap, N. Dyakonova, D. But, F. Teppe, M. Sypek, J. Suszek, A. Wolos, G. Cywinski, K.Szkudlarek, I.Yahniuk, **“Physics and Applications of Field Effect Transistors for Terahertz Imaging”**,Energy Materials Nanotechnology Meeting on Terahertz 2016 San Sebastian, Spain, May 14-18, 2016
23. W. Knap, M. Sypek, D. B. But, N. Dyakonova, D. Coquillat, F. Teppe, E. Kling, **“Terahertz Imaging with Nanometer Field Effect Transistors for Security Screening”**, Paris –OPTRO 7th International Symposium on Optronics in Defense and Security, Paris 2-4 February, 2016
24. W. Knapet al., **“Terahertz science and technology - achievements and future perspectives of French-Polish collaborative projects”**, French-Polish Forum of Research and Innovations, Krakow, 8 June, 2016.
25. W. Knap, D. B. But, N. Dyakonova, D. Coquillat, F. Teppe, M. Vitiello, S. D. Ganichev, M. Sypek, **“Terahertz Detectors Based on Plasma Oscillations in Nanometer Field Effect Transistors”**, 9th Workshop on Frontiers in Electronics (WOFE-2015) will be held on December 15-18, 2015, in the Caribe Hilton Hotel, San Juan, Puerto Rico, USA.
26. W. Knap, J. Suszek, D. Coquillat, G. Cywinski, N. Dyakonova, F. Teppe, M. Sypek, **“Terahertz Plasma FETs from Basic Physics to First Fast Terahertz Scanners for Detection of Explosives and CBRN”**, NATO ARW on THz Diagnostics of CBRN effects and Detection of Explosives & CBRN, Izmir, Turkey, 3-6 November 2015
27. W. Knap, and M. Sypek **“Terahertz Imaging with Field Effect Transistors”,**European Microwave Week EuMW Paris September 6-11, 2015
28. *(plenary)* W. Knap **“Terahertz Imaging and Broadband Wireless Communication Using Plasma Oscillations in Nanometer Field Effect Transistors”**, 2nd International Conference on Applied Science and Environmental Technology, Bangkok, Thailand, August 2015
29. *(plenary)*W. Knap et al **“From Basic Physics to Applications of THz Nanotransistors”**,4th Russian-Japan-USA Symposium (RJUS-2015) on Fundamental & Applied Problems of Terahertz Devices & Technologies "RJUS TeraTech-2015", Chernogolovka, Russia, June 9-12, 2015
30. *(plenary)* W. Knap **“Terahertz Excitations in Terahertz Nanotransistors”**, 19th Symposium on Nanophysics an Nanotechnology, Nizhny Novgorod, Russia, March 10-14, 2015
31. W. Knap et al **“Plasma Oscillations in Field Effect Transistors for Room Temperature Terahertz Imaging Applications”**, 3rd International Symposium on Microwave/THz Science and Technology MTSA 2015, Okinawa, Japan, June 30 – July 4, 2015
32. W. Knap et al **“Terahertz Detection by Plasma Waves Nonlinearities – in semiconductors and topological insulator systems”**, Russian Conference on Semiconductor Photonic Problems, Novosibirsk, Russia, October 12-16, 2015
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